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AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Original) A manufacturing method for a display device comprising:
 - a step for providing a source line around a pixel electrode provided on a substrate;
 - a step for forming an insulating film pattern having openings for a source and a drain;
 - a step for forming the source and the drain; and
 - a step for providing a semiconductor film on the source and the drain; and
 - a step for providing a gate on the semiconductor film;wherein the respective steps are implemented substantially under atmospheric pressure.

2. (Original) The manufacturing method according to Claim 1, further comprising a step for electrolytically plating the source line.

3. (Original) The manufacturing method according to Claim 1, further comprising a step for providing a film for protecting the gate and a step for applying electrophoretic ink after the film is provided.

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4. (Original) The manufacturing method according to Claim 3, wherein the film is provided by laminating in the step for providing the film for protecting the gate.

5. - 9. (Cancelled).

6. 10. (Previously Presented) A manufacturing method for a display device, the method comprising:

forming a source line on a substrate;

forming a source and a drain of a transistor on the substrate;

forming a semiconductor film contacting the source and the drain; and

providing a gate of the transistor;

wherein the source line, the source, the drain, the semiconductor film, and the gate are implemented substantially under atmospheric pressure.

7. 11. (Previously Presented) The manufacturing method according to Claim 10, the forming of source line is implemented by electrolytic plating.

8. 12. (Previously Presented) The manufacturing method according to Claim 10, further comprising:

forming a film covering the gate; and

applying an electrophoretic ink to the film.

9 13. (Previously Presented) The manufacturing method according to Claim 12, the forming of the film is implemented by lamination coating.

10 14. (Previously Presented) The manufacturing method according to Claim 10, the substrate is a resin film with the pixel electrode.

15. - 17. (Cancelled)

5 18. (Previously Presented) The manufacturing method according to Claim 1, the semiconductor film being formed over the source and the drain.

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19. (Previously Presented) A manufacturing method for a display device, the method comprising:

forming a source line on a substrate;

forming a source and a drain which are included in a transistor and one of which contacts the source line;

forming a semiconductor film over the source and the drain, the semiconductor film contacting the source and the drain; and

forming a gate of the transistor above the semiconductor film.

10 20. (Previously Presented) The method according to Claim 19, further comprising:

forming a pixel electrode on the substrate that contacts the other of the source and the drain.

~~13~~ 21. (Previously Presented) The method according to Claim 19, further comprising:

forming an insulating film on the substrate, at least a part of the insulating film disposed between the source and the drain.

~~14~~ 22. (Previously Presented) The method according to Claim 19, further comprising:

forming a pixel electrode on the substrate that contacts the other of the source and the drain;

at least a part of one of the source and the drain covering at least a part of the pixel electrode; and

the insulating film being covered by at least a part of the semiconductor film.

~~15~~ 23. (Previously Presented) The manufacturing method according to Claim 19, further comprising forming a pixel electrode on the substrate that contacts the other of the source and the drain, the pixel electrode being formed between the semiconductor film and the substrate.

14b 24. (Previously Presented) A manufacturing method for a display device, comprising:

forming a source line on a substrate;

forming a source and a drain which are included in a transistor and one of which contacts the source line;

forming a pixel electrode on the substrate that contacts the other of the source and the drain;

forming a semiconductor film over the pixel electrode, the pixel electrode being formed between the semiconductor film and the substrate.